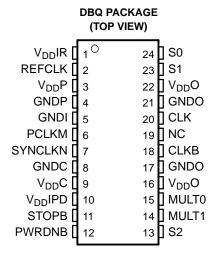


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DIRECT RAMBUS™ CLOCK GENERATOR

FEATURES

- 533-MHz Differential Clock Source for Direct Rambus™ Memory Systems for an 1066-MHz Data Transfer Rate
- Fail-Safe Power Up Initialization
- Synchronizes the Clock Domains of the Rambus Channel With an External System or Processor Clock
- Three Power Operating Modes to Minimize Power for Mobile and Other Power-Sensitive Applications
- Operates From a Single 3.3-V Supply and 120 mW at 300 MHz (Typ)
- Packaged in a Shrink Small-Outline Package (DBQ)
- Supports Frequency Multipliers: 4, 6, 8, 16/3
- No External Components Required for PLL
- Supports Independent Channel Clocking
- Spread Spectrum Clocking Tracking Capability to Reduce EMI
- Designed for Use With TI's 133-MHz Clock Synthesizers CDC924 and CDC921
- Cycle-Cycle Jitter Is Less Than 40 ps at 533 MHz
- Certified by Gigatest Labs to Exceed the Rambus DRCG Validation Requirement
- Supports Industrial Temperature Range of –40°C to 85°C



NC - No internal connection

DESCRIPTION

The Direct Rambus clock generator (DRCG) provides the necessary clock signals to support a Direct Rambus memory subsystem. It includes signals to synchronize the Direct Rambus channel clock to an external system or processor clock. It is designed to support Direct Rambus memory on a desktop, workstation, server, and mobile PC motherboards. DRCG also provides an off-the-shelf solution for a broad range of Direct Rambus memory applications.

The DRCG provides clock multiplication and phase alignment for a Direct Rambus memory subsystem to enable synchronous communication between the Rambus channel and ASIC clock domains. In a Direct Rambus memory subsystem, a system clock source provides the REFCLK and PCLK clock references to the DRCG and memory controller, respectively. The DRCG multiplies REFCLK and drives a high-speed BUSCLK to RDRAMs and the memory controller. Gear ratio logic in the memory controller divides the PCLK and BUSCLK frequencies by ratios M and N such that PCLKM = SYNCLKN, where SYNCLK = BUSCLK/4. The DRCG detects the phase difference between PCLKM and SYNCLKN and adjusts the phase of BUSCLK such that the skew between PCLKM and SYNCLKN is minimized. This allows data to be transferred across the SYNCLK/PCLK boundary without incurring additional latency.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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User control is provided by multiply and mode selection terminals. The multiply terminals provide selection of one of four clock frequency multiply ratios, generating BUSCLK frequencies ranging from 267 MHz to 533 MHz with clock references ranging from 33 MHz to 100 MHz. The mode select terminals can be used to select a bypass mode where the frequency multiplied reference clock is directly output to the Rambus channel for systems where synchronization between the Rambus clock and a system clock is not required. Test modes are provided to bypass the PLL and output REFCLK on the Rambus channel and to place the outputs in a high-impedance state for board testing.

The CDCFR83A has a fail-safe power up initialization state-machine which supports proper operation under all power up conditions.

The CDCFR83A is characterized for operation over free-air temperatures of -40°C to 85°C.

FUNCTIONAL BLOCK DIAGRAM PWRDWNB S0 S2 **STOPB Test MUX Bypass MUX ByPCLK PLLCLK** CLK PLL Phase **CLKB REFCLK** В Aligner **PACLK** $\varphi_{\boldsymbol{D}}$ 2 PCLKM | SYNCLKN **MULTO**

FUNCTION TABLE(1)

MODE	S0	S 1	S2	CLK	CLKB
Normal	0	0	0	Phase aligned clock	Phase aligned clock B
Bypass	1	0	0	PLLCLK	PLLCLKB
Test	1	1	0	REFCLK	REFCLKB
Output test (OE)	0	1	Х	Hi-Z	Hi-Z
Reserved	0	0	1	_	_
Reserved	1	0	1	_	_
Reserved	1	1	1	Hi-Z	Hi-Z

(1) X = don't care, Hi-Z = high impedance

MULT1



TERMINAL FUNCTIONS

TERMINAL		1/0	DECODINE	
NAME	NO.	I/O	DESCRIPTION	
CLK	20	0	Output clock	
CLKB	18	0	Output clock (complement)	
GNDC	8		GND for phase aligner	
GNDI	5		GND for control inputs	
GNDO	17, 21		GND for clock outputs	
GNDP	4		GND for PLL	
MULT0	15	I	PLL multiplier select	
MULT1	14	I	PLL multiplier select	
NC	19		Not used	
PCLKM	6	ı	Phase detector input	
PWRDNB	12	_	Active low power down	
REFCLK	2	I	Reference clock	
S0	24	I	Mode control	
S1	23	I	Mode control	
S2	13	_	Mode control	
STOPB	11	_	Active low output disable	
SYNCLKN	7	I	Phase detector input	
$V_{DD}C$	9		V _{DD} for phase aligner	
V _{DD} IPD	10		Reference voltage for phase detector inputs and STOPB	
$V_{DD}IR$	1		Reference voltage for REFCLK	
V _{DD} O	16, 22		V _{DD} for clock outputs	
$V_{DD}P$	3		V _{DD} for PLL	



PLL DIVIDER SELECTION

Table 1 lists the supported REFCLK and BUSCLK frequencies. Other REFCLK frequencies are permitted, provided that (267 MHz < BUSCLK < 533 MHz) and (33 MHz < REFCLK < 100 MHz).

Table 1. REFCLK and BUSCLK Frequencies

MULT0	MULT1	REFCLK (MHz)	MULTIPLY RATIO	BUSCLK ⁽¹⁾ (MHz)
0	0	67	4	267
0	1	50	6	300
0	1	67	6	400
1	1	33	8	267
1	1	50	8	400
1	1	67	8	533
1	0	67	16/3	356

⁽¹⁾ BUSCLK will be undefined until a valid reference clock is available at REFCLK. After applying REFCLK, the PLL requires stabilization time to achieve phase lock.

Table 2. Clock Output Driver States

STATE	PWRDNB	STOPB	CLK	CLKB
Powerdown	0	X	GND	GND
CLK stop	1	0	V _{X, STOP}	$V_{X, STOP}$
Normal	1	1	PACLK/PLLCLK/REFCLK ⁽¹⁾	PACLKB/PLLCLKB/REFCLKB

⁽¹⁾ Depending on the state of S0, S1, and S2

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

		UNIT
V_{DD}	Supply voltage range ⁽²⁾	–0.5 V to 4 V
Vo	Output voltage range at any output terminal	-0.5 V to V _{DD} + 0.5 V
V_{I}	Input voltage rangeat any input terminal	–0.5 V to V _{DD} + 0.5 V
	Continuous total power dissipation	See Dissipation Rating Table
T_A	Operating free-air temperature range	-40°C to 85°C
T _{stg}	Storage temperature range	−65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS

PACKAGE	T _A ≤ 25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C ⁽¹⁾	POWER RATING	POWER RATING
DBQ	1400 mW	11 mW/°C	905 mW	740 mW

⁽¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

⁽²⁾ All voltage values are with respect to the GND terminals.



RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage	3.135	3.3	3.465	V
V_{IH}	High-level input voltage (CMOS)	$0.7 \times V_{DD}$			V
V_{IL}	Low-level input voltage (CMOS)			$0.3 \times V_{DD}$	V
	Initial phase error at phase detector inputs (required range for phase aligner)	$-0.5 \times t_{c(PD)}$		$0.5 \times t_{c(PD)}$	V
V_{IL}	REFCLK low-level input voltage			$0.3 \times V_{DD}IR$	V
V_{IH}	REFCLK high-level input voltage	$0.7 \times V_{DD}IR$			V
V_{IL}	Input signal low voltage (STOPB)			$0.3 \times V_{DD}IPD$	V
V_{IH}	Input signal high voltage (STOPB)	$0.7 \times V_{DD}IPD$			V
	Input reference voltage for (REFCLK) (V _{DD} IR)	1.235		3.465	V
	Input reference voltage for (PCLKM and SYSCLKN) (V _{DD} IPD)	1.235		3.465	V
I _{OH}	High-level output current			-16	mA
I _{OL}	Low-level output current			16	mA
T _A	Operating free-air temperature	-40		85	°C

TIMING REQUIREMENTS

		N	IIN	MAX	UNIT
t _{c(in)}	Input cycle time		10	40	ns
	Input cycle-to-cycle jitter			250	ps
	Input duty cycle over 10,000 cycles	40	0%	60%	
f _{mod}	Input frequency modulation		30	33	kHz
	Modulation index, nonlinear maximum 0.5%			0.6%	
	Phase detector input cycle time (PCLKM and SYNCLKN)		30	100	ns
SR	Input slew rate		1	4	V/ns
	Input duty cycle (PCLKM and SYNCLKN)	25	5%	75%	



ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETE	R	TEST CON	DITIONS ⁽¹⁾	MIN	TYP ⁽²⁾	MAX	UNIT
V _{O(STOP)}	Output voltage during	CLK Stop (STOPB = 0)	See Figure 1		1.1		2	
$V_{O(X)}$	Output crossing-point	voltage	See Figure 1 and F	igure 6	1.3		1.8	V
Vo	Output voltage swing		See Figure 1		0.4		0.6	V
V_{IK}	Input clamp voltage		$V_{DD} = 3.135 \text{ V},$	$I_I = -18 \text{ mA}$			-1.2	V
			See Figure 1				2	
V_{OH}	High-level output volta	age	V_{DD} = min to max,	$I_{OH} = -1 \text{ mA}$	V _{DD} - 0.1			V
			$V_{DD} = 3.135 \text{ V},$	$I_{OH} = -16 \text{ mA}$	2.4			
İ			See Figure 1		1			
V_{OL}	Low-level output volta	ge	V_{DD} = min to max,	$I_{OH} = 1 \text{ mA}$			0.1	V
			$V_{DD} = 3.135 \text{ V},$	$I_{OH} = 16 \text{ mA}$			0.5	
i			$V_{DD} = 3.135 V,$	$V_O = 1 V$	-32	– 52		
I_{OH}	High-level output curr	ent	$V_{DD} = 3.3 V,$	$V_0 = 1.65 \text{ V}$		– 51		mA
			$V_{DD} = 3.465 \text{ V},$	$V_0 = 3.135 \text{ V}$		-14.5	-21	
			$V_{DD} = 3.135 V,$	$V_0 = 1.95 \text{ V}$	43	61.5		
I_{OL}	Low-level output curre	ent	$V_{DD} = 3.3 V,$	$V_0 = 1.65 \text{ V}$		65		mA
			$V_{DD} = 3.465 \text{ V},$	$V_0 = 0.4 \ V$		25.5	36	
I_{OZ}	High-impedance-state	output current	S0 = 0, S1 = 1				±10	μΑ
I _{OZ(STOP)}	High-impedance-state output current during CLK stop		Stop = 0, $V_O = GNE$	O or V _{DD}			±100	μΑ
I _{OZ(PD)}	High-impedance-state output current in power-down state		PWRDNB = 0, V _O =	= GND or V _{DD}	-10		100	μΑ
	High-level input	REFCLK, PCLKM, SYNCLKN, STOPB	$V_{DD} = 3.465 \text{ V}, \qquad V_{I} = V_{DD}$				10	
I _{IH}	current	PWRDNB, S0, S1, S2, MULT0, MULT1	$V_{DD} = 3.465 V,$	v _I = v _{DD}			10	- μΑ
	Low-level input	REFCLK, PCLKM, SYNCLKN, STOPB	V 0.405.V				-10	•
I _{IL}	current	PWRDNB, S0, S1, S2, MULT0, MULT1	$V_{DD} = 3.465 \text{ V},$	V ₁ = 0			-10	μΑ
7	Outrot increased	High state	R _I at I _O - 14.5 mA to	o –16.5 mA	15	35	50	
Z_{O}	Output impedance	Low state	R _I at I _O 14.5 mA to	16.5 mA	11	17	35	Ω
	Defenses assument	V ID V IDD	V 2.405.V	PWRDNB = 0			50	μΑ
	Reference current	$V_{DD}IR$, $V_{DD}IPD$	$V_{DD} = 3.465 \text{ V}$	PWRDNB = 1			0.5	mA
Cı	Input capacitance	ut capacitance		$V_I = V_{DD}$ or GND		2		pF
Co	Output capacitance		V _O = V _{DD} or GND			3		pF
I _{DD(PD)}	Supply current in pwo	er-down state	REFCLK = 0 MHz to 100 MHz, PWDNB = 0, STOPB = 1				100	μΑ
I _{DD(CLKSTOP)}	Supply current in CLK	stop state	BUSCLK configured	d for 533 MHz			45	mA
I _{DD(NORMAL)}	Supply current in norr	nal state	BUSCLK = 533 MH	lz			100	mA

 V_{DD} refers to any of the following; $V_{DD},\,V_{DD}IPD,\,V_{DD}IR,\,V_{DD}O,\,V_{DD}C,$ and $V_{DD}P$ All typical values are at V_{DD} = 3.3 V, T_A = 25°C.



SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER				TEST CONDITIONS	MIN	TYP ⁽¹⁾ MAX	UNIT
t _{c(out)}	Clock output cycle time				1.87	3.75	ns
			267 MHz			80	
		Infinite and	300 MHz	Can Figure 2		70	
t _(jitter)	Total cycle jitter over 1, 2, 3, 4, 5, or 6 clock cycles	stopped phase	356 MHz	See Figure 3		60	ps
	3, 4, 3, 01 0 0100K cycles	alignment	400 MHz			50	
			533 MHz ⁽²⁾			40	
t _(phase)	Phase detector phase error for distributed loop		Static phase error ⁽³⁾	-100	100	ps	
t _(phase, SSC)	PLL output phase error whe	en tracking SSC		Dynamic phase error ⁽³⁾	-100	100	ps
I _(DC)	Output duty cycle over 10,0	00 cycles		See Figure 4	45%	55%	
			267 MHz			80	
		Infinite and	300 MHz			70	
t _(DC, err)	Output cycle-to-cycle duty cycle error	stopped phase	356 MHz	See Figure 5		60	ps
	dydio difor	alignment	400 MHz			50	
			533 MHz				
t _r , t _f	Output rise and fall times (measured at 20%–80% of output voltage)		See Figure 7	160	400	ps	
Δt	Difference between rise and fall times on a single device (20%–80%) $ t_{\rm f}-t_{\rm f} $			See Figure 7		100	ps

STATE TRANSITION LATENCY SPECIFICATIONS

	PARAMETER		то	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _(powerup)	Delay time, PWRDNB↑ to CLK/CLKB output settled (excluding t _(DISTLOCK))	Powerdown	Normal	See Figure 8			3	ms
	Delay time, PWRDNB↑ to internal PLL and clock are on and settled	Powerdown	Noma				3	ms
t _(VDDpowerup)	Delay time, power up to CLK/CLKB output settled	V	Normal	See Figure 8			3	ms
	Delay time, power up to internal PLL and clock are on and settled	V DD	V _{DD} Normal				3	1115
t _(MULT)	MULT0 and MULT1 change to CLK/CLKB output resettled (excluding t _(DISTLOCK))	Normal	Normal	See Figure 9			1	ms
t _(CLKON)	STOPB [↑] to CLK/CLKB glitch-free clock edges	CLK Stop	Normal	See Figure 10			10	ns
t(CLKSETL)	STOPB↑ to CLK/CLKB output settled to within 50 ps of the phase before STOPB was disabled	CLK Stop	Normal	See Figure 10			20	cycles
t _(CLKOFF)	STOPB↓ to CLK/CLKB output disabled	Normal	CLK Stop	See Figure 10			5	ns
t _(powerdown)	Delay time, PWRDNB↓ to the device in the power-down mode	Normal	Powerdown	See Figure 8			1	ms
t _(STOP)	Maximum time in CLKSTOP (STOPB = 0) before reentering normal mode (STOPB = 1)	STOPB	Normal	See Figure 10			100	μs
t _(ON)	Minimum time in normal mode (STOPB = 1) before reentering CLKSTOP (STOPB = 0)	Normal	CLK Stop	See Figure 10	100		_	ms
t _(DISTLOCK)	Time from when CLK/CLKB output is settled to when the phase error between SYNCLKN and PCLKM falls within $t_{(phase)}$	Unlocked	Locked				5	ms

⁽¹⁾ All typical values are at V_{DD} = 3.3 V, T_A = 25°C.

 ⁽¹⁾ All typical values are at V_{DD} = 3.3 V, T_A = 25°C.
(2) Jitter measurement according to Rambus validation specification
(3) Assured by design



PARAMETER MEASUREMENT INFORMATION

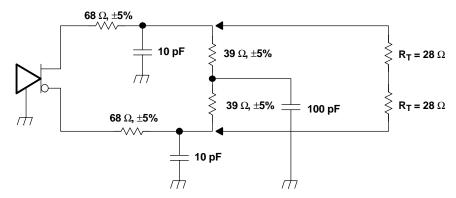
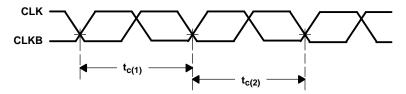
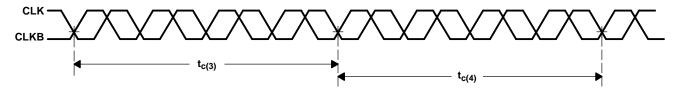


Figure 1. Test Load and Voltage Definitions ($V_{O(STOP)}$, $V_{O(X)}$, V_{O} , V_{OH} , V_{OL})



Cycle-to-cycle jitter = $|t_{c(1)} - t_{c(2)}|$ over 10000 consecutive cycles

Figure 2. Cycle-to-Cycle Jitter



Cycle-to-cycle jitter = $|t_{c(3)} - t_{c(4)}|$ over 10000 consecutive cycles

Figure 3. Short Term Cycle-to-Cycle Jitter Over Four Cycles

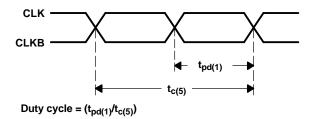


Figure 4. Output Duty Cycle



PARAMETER MEASUREMENT INFORMATION (continued)

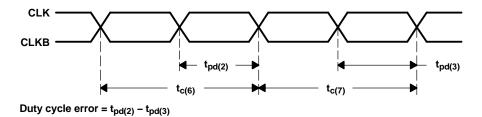


Figure 5. Duty Cycle Error (Cycle-to-Cycle)

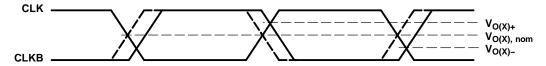


Figure 6. Crossing-Point Voltage



Figure 7. Voltage Waveforms

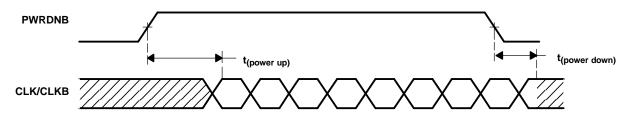


Figure 8. PWRDNB Transition Timings

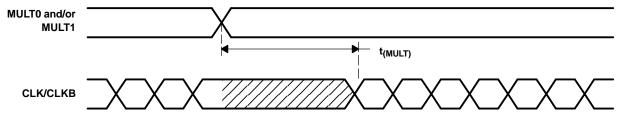
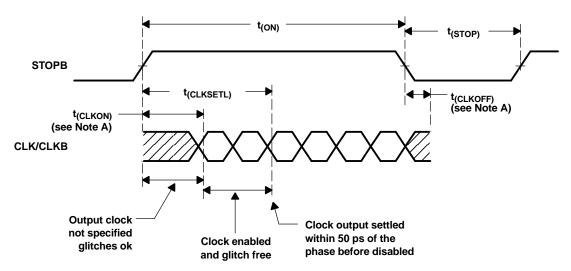


Figure 9. MULT Transition Timings



PARAMETER MEASUREMENT INFORMATION (continued)



A. $V_{ref} = V_O \pm 200 \text{ mV}$

Figure 10. STOPB Transition Timings

PACKAGE MATERIALS INFORMATION

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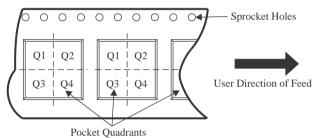
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

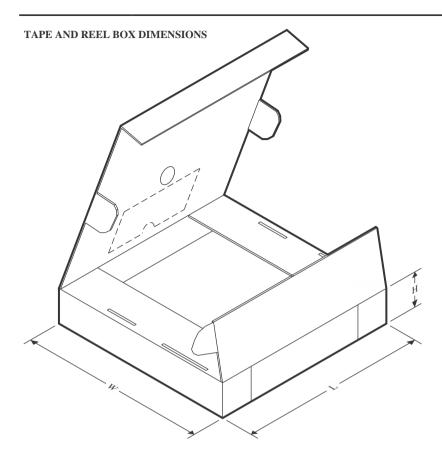


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCFR83ADBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

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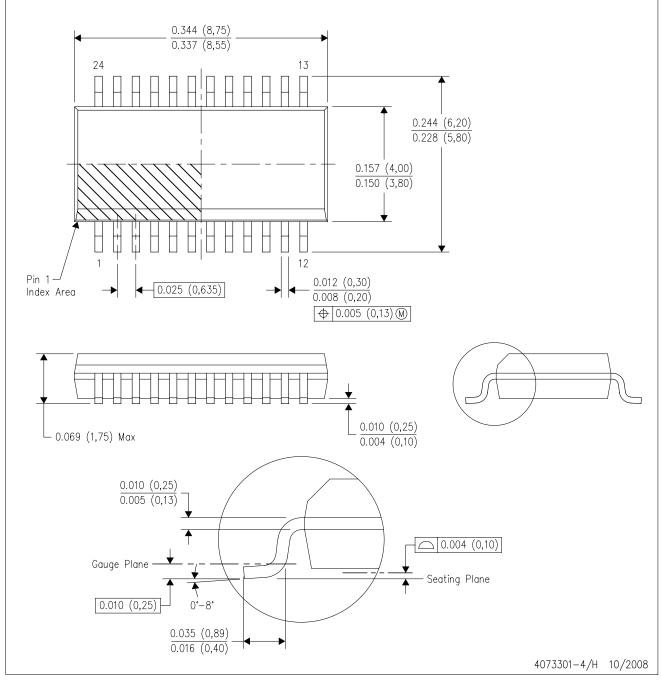


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CDCFR83ADBQR	SSOP	DBQ	24	2500	356.0	356.0	35.0	

DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
- D. Falls within JEDEC MO-137 variation AE.



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